Unitized Semiconductor Devices - Page 1 of 1



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| Inclosure Materia | |
|-------------------------|--|
| Ceramic | |
| Overall Length: | |
| 0.785 inches | |
| Overall Height: | |
| 0.200 inches | |
| Overall Width: | |
| 0.325 inches | |
| Joint Electronic D | evice Engineering Council/jedec/case Outline Designation: |
| To-116 | |
| Component Name | And Quantity: |
| 4 transistor | |
| Mounting Method | : |
| Terminal | |
| Semiconductor M | aterial: |
| Silicon all transisto | r |
| Voltage Rating In | Volts Per Characteristic: |
| 40.0 collector to ba | ase voltage/static/emitter open all transistor and 15.0 collector to emitter voltage/static/base open all transistor and 4.5 |
| emitter to base vol | age, static, collector open all transistor |
| Current Rating Pe | er Characteristic: |
| 500.00 milliampere | s source cutoff current all transistor |
| Power Rating Per | Characteristic: |
| 1.5 watts small-sig | nal input power, common-collector absolute all semiconductor |
| Special Features: | |
| All transistor junction | on pattern arrangement: npn |
| Terminal Type An | d Quantity: |
| 14 pin | |
| Shelf Life: | |
| N/a | |
| Unit Of Measure: | |
| | |
| Demilitarization: | |
| No | |
| Fiig: | |
| A110a0 | |